



General Description

The AOZ9004D is a battery protection IC with integrated dual common-drain N-channel MOSFET. The device includes accurate voltage detectors and delay circuits, and is suitable for protecting single-cell lithium-ion / lithium-polymer rechargeable battery packs from overcharge, over-discharge, and over-current conditions.

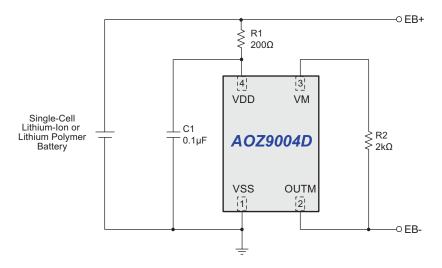
The AOZ9004D is available in a 2mm x 5mm 4-pin DFN package and is rated over a -40°C to +85°C ambient temperature range.

Features

- Integrated common-drain N-channel MOSFET
- High-accuracy voltage detection circuit
 - Overcharge detection accuracy ±25mV (+25°C), ±30 mV (-5°C to +55°C)
 - Overcharge release accuracy ±50mV
 - Over-discharge detection accuracy ±50mV
 - Over-discharge release accuracy ±100mV
 - Discharge over-current detection accuracy ±15mV
 - Load short-circuit detection accuracy ±200mV
- ±20% accurate internal detection delay times (external capacitors are unnecessary)
- Charger connection pin withstands up to 28V
- Wide operating temperature range: -40°C to +85°C
- Low current consumption
- 3.0mA (typ.), 5.5mA (max.) in operation mode at +25°C
- Small 2mm x 5mm 4-pin DFN package

Applications

- Lithium-ion rechargeable battery packs
- Lithium-polymer rechargeable battery packs





Rev. 1.0 October 2006

Typical Application

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Ordering Information

Part Number	Overcharge Detection Voltage (V _{CU})	Overcharge Release Voltage (V _{CL})	Over- discharge Detection Voltage (V _{DL})	Over- discharge Release Voltage (V _{DU})	Discharge Over- current Threshold (I _{DIO})	Charge Over- current Threshold (I _{CIO})	0V Battery Charge Function	Shutdown Function
AOZ9004DI-00	4.275V	4.175V	2.3V	2.4V	2A	2A	Yes	Yes
AOZ9004DI-01	4.280V	4.130V	2.8V	3.1V	2A	2A	No	Yes



All AOS Products are offering in packaging with Pb-free plating and compliant to RoHS standards. Please visit wwww.aosmd.com/web/rohs_compliant.jsp for additional information.

Table 1. Delay Time Combination⁽¹⁾

Delay Time Combination	Overcharge Detection Delay Time (t _{CU})	Over-discharge Detection Delay Time (t _{DL})	Discharge Over-current Detection Delay Time (t _{DIOV})	Charge Over- current Detection Delay Time (t _{CIOV})	Load Short- circuiting Detection Delay Time (t _{SHORT})
1	1.2s	150ms	9ms	9ms	560us
2 ⁽²⁾	1.2s	150ms	9ms	9ms	300us
3	142ms	38ms	18ms	9ms	300us
4	1.2s	150ms	18ms	9ms	300us
5	1.2s	38ms	9ms	9ms	300us

Notes:

1. The delay times can have the range specified in Table 2. Please contact our Sales department if you wish to order non-standard values and for additional information.

2. Combination 2 is the default delay time combination for AOZ9004DI-00 and AOZ9004DI-01.

Table 2. Delay Time Selection Range⁽³⁾

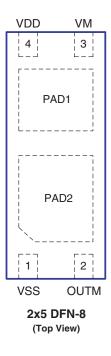
Symbol	Delay Time	Selection Range			
t _{CU}	Overcharge detection delay time	143ms	573ms	1.2s	
t _{DL}	Over-discharge detection delay time	38ms	150ms	300ms	
t _{DIOV}	Discharge over-current detection delay time	4.5ms	9ms	18ms	
t _{CIOV}	Charge over-current detection delay time	4.5ms	9ms	18ms	
t _{SHORT}	Load short-circuiting detection delay time	_	300us	560us	

Note:

3. The values in Bold are standard values. Please contact our Sales department if you wish to order non-standard values and for additional information.



Pin Configuration



Pin Description

Pin Number	Pin Name	Pin Function
1	VSS	Ground. VSS is the source of the internal Discharge MOSFET. Connect VSS directly to the cathode of lithium-ion/lithium polymer battery cell.
2	OUTM	Output Pin. OUTM is the source of the internal Charge MOSFET. Connect OUTM directly to the negative terminal of the battery pack.
3	VM	Over-current / Charger Detection Pin. Connect a 2kW resistor between VM and the negative terminal of the battery pack.
4	VDD	Input Supply Pin. Connect a 0.1uF capacitor between VDD and VSS.
PAD1	DO	Discharge MOSFET Gate. This pad is for test purposes only. Always leave this pad unconnected.
PAD2	Drain	MOSFET Common-Drain Connection. This pad is for test purposes only. Always leave this pad unconnected.



AOZ9004D

Block Diagram

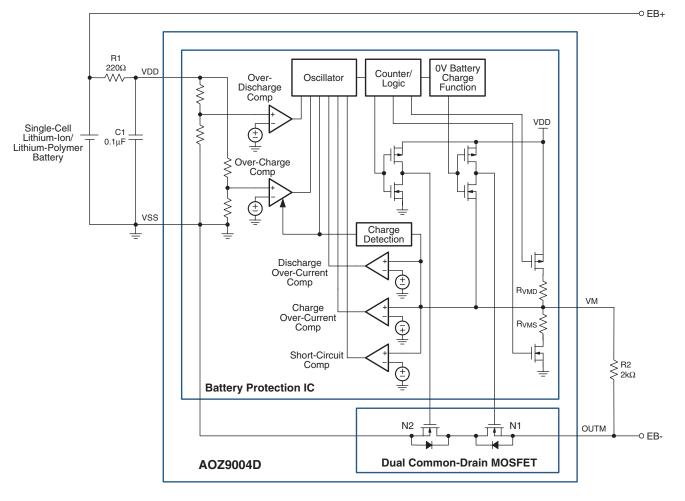


Figure 1. AOZ9004D Function Block Diagram

Absolute Maximum Ratings

Exceeding the Absolute Maximum ratings may damage the device.

Parameter	Rating
V _{DD} to V _{SS}	-0.3V to +12V
V _M to V _{DD}	-28V to +0.3V
MOSFET Gate-to-Source Voltage	-0.3V to +12V
Continuous Drain Current ⁽⁴⁾ ($R_{\theta JA} = 84^{\circ}C/W$, $T_A = 25^{\circ}C$) ($R_{\theta JA} = 84^{\circ}C/W$, $T_A = 85^{\circ}C$)	4.8A 3.4A
Pulsed Drain Current	30A
Storage Temperature (T _S)	-55°C to +125°C
Operating Temperature (T _A)	-40°C to +85°C
Power Dissipation ⁽⁴⁾ $(R_{\theta JA} = 84^{\circ}C/W, T_A = 25^{\circ}C)$ $(R_{\theta JA} = 84^{\circ}C/W, T_A = 85^{\circ}C)$	1.4W 0.7W

Note:

4. The value of R_{0JA} is measured with the device mounted on 1-in² FR-4 board with 2-oz. copper, in a still air environment with $T_A = 25^{\circ}$ C. The value in any given application depends on the user's specific board design.



Electrical Characteristics

 $T_A = 25^{\circ}$ C unless otherwise specified. Parameters specified over $T_A = -40^{\circ}$ C to $+85^{\circ}$ C are guaranteed by design only and not production tested.

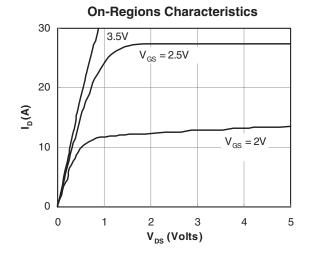
Symbol	Parameter	Condition		Min.	Тур.	Max.	Unit
DETECTIO							
V _{CU}	Overcharge Detection Voltage	T _A = 25°C		V _{CU} -0.025	V _{CU}	V _{CU} +0.025	V
		$T_A = -5^{\circ}C$ to -	+55°C	V _{CU} –0.03	V _{CU}	V _{CU} +0.03	V
		$T_A = -40^{\circ}C$ to	+85°C	V _{CU} -0.060	V _{CU}	V _{CU} +0.040	V
V _{CL}	Overcharge Release Voltage	V _{CL} ≠V _{CU}	$T_A = 25^{\circ}C$	V _{CL} -0.05	V _{CL}	VCL+0.05	V
			$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$	V _{CL} 08	V _{CL}	V _{CL}	V
		$V_{CL} = V_{CU}$	$T_A = 25^{\circ}C$	V _{CL} -0.025	V _{CL}	V _{CL} +0.025	V
			$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$	V _{CL} -0.06	V _{CL}	V _{CL} +0.04	V
V _{DL}	Over-Discharge Detection	T _A = 25°C	ł	V _{DL} -0.05	V _{DL}	V _{DL} +0.05	V
	Voltage (2.0 to 3.0 V, Adjustable)			V _{DL} -0.11	V _{DL}	V _{DL} +0.13	V
V _{DU}	Over-Discharge Release	V _{DU} ≠V _{DL}	$T_A = 25^{\circ}C$	V _{DU} -0.10	V _{DU}	V _{DU} +0.10	V
	Voltage (2.0 to 3.40 V, Adjustable)		$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$	V _{DU} -0.15	V _{DU}	V _{DU} + 0.19	V
Adjustab	Aujustable)	$V_{DU} = V_{DL}$	$T_A = 25^{\circ}C$	V _{DU} -0.05	V _{DU}	V _{DU} +0.05	V
			$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$	V _{DU} -0.11	V _{DU}	V _{DU} +0.13	V
V _{DIOV}	Discharge Over-Current Threshold	$T_A = 25^{\circ}C$		V _{DIOV} -0.015	V _{DIO} v	V _{DIOV} +0.015	V
		$T_A = -40^{\circ}C$ to $+85^{\circ}C$		V _{DIOV} -0.021	V _{DIO} v	V _{DIOV} +0.024	V
V _{SHORT}	Load Short-Circuiting	$T_A = 25^{\circ}C$		0.35	0.50	0.65	V
	Detection Voltage	$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$		0.3	0.5	0.7	V
V _{CIOV}	Charge Over-Current Threshold	$T_A = 25^{\circ}C$		-0.13	-0.1	-0.07	V
		$T_A = -40^{\circ}C$ to	+85°C	-0.14	-0.1	-0.06	V
OV BATTE	RY CHARGE FUNCTION	1					
V _{0INH}	0V Battery Charge Inhibition Bat-	T _A = 25°C				0.5	V
	tery Voltage (0V battery charg- ing function "unavailable")	$T_{A} = -40^{\circ}C \text{ to } +85^{\circ}C$				0.3	V
V _{0CHA}	0 V Battery Charge Starter	T _A = 25°C		1.2			V
	Battery Voltage (0V battery charging function "available")	$T_A = -40^{\circ}C$ to	+85°C	1.7			V
INPUT VOI	TAGE						
V _{DSOP1}	Operating Voltage Between VDD Pin and VSS Pin	Internal Circu	it Operating Voltage	1.5		8	V
V _{DSOP2}	Operating voltage between VDD pin and VM pin	Internal Circuit Operating Voltage		1.5		28	V
INPUT CU	RRENT (No Shutdown Function)	•					
I _{OPE}	Current Consumption During	V _{DD} = 3.5V, \	/ _{VM} = 0V	1.0	3.0	5.5	uA
	Operation	$T_A = -40^{\circ}C$ to	+85°C	0.7	3.0	6.0	uA
I _{OPED}	Current Consumption During	$V_{DD} = V_{VM} =$	1.5V	0.3	2.0	3.5	uA
	Over-Discharge	$T_A = -40^{\circ}C$ to	+85°C	0.2	2.0	3.8	uA

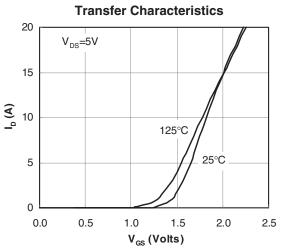


Electrical Characteristics (Continued) $T_A = 25^{\circ}C$ unless otherwise specified. Parameters specified over $T_A = -40^{\circ}C$ to $+85^{\circ}C$ are guaranteed by design only and not production tested.

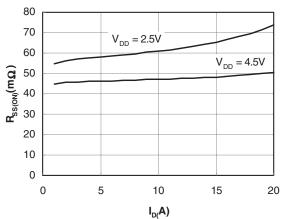
Symbol	Parameter	Condition	Min.	Тур.	Max.	Unit
	RRENT (Shutdown Function)					
I _{OPE}	Current Consumption During	V _{DD} = 3.5V, V _{VM} = 0V	1.0	3.0	5.5	uA
	Operation	$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$	0.7	3.0	6.0	uA
I _{PDN}	Current Consumption at	$V_{DD} = V_{VM} = 1.5V$			0.2	uA
	Shutdown	$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$			0.3	uA
INTEGRAT	ED MOSFET	•	ŀ	1		
BV_{DS_C}	Charge Control MOSFET Drain-Source Breakdown	V _{DD} = V _{CU}	30			V
I _{LEAK_C}	Charge Control MOSFET Leakage	$V_{DD} = V_{CU}$		1		mA
BV _{DS_D}	Discharge Control MOSFET Drain-Source Breakdown Voltage	$V_{DD} = V_{DL}$	30			V
I _{LEAK_D}	Discharge Control MOSFET Leakage Current	$V_{DD} = V_{DL}$		1		mA
R_{SS}	Total Output Resistance (OUTM to V _{SS})	V _{DD} = 3.5V, I _{OUT} = 1.5A		48	60	mΩ
DETECTIC	ON DELAY TIME (Combination 2 pe	er Table 1)				•
t _{CU}	Overcharge Detection Delay	$T_A = 25^{\circ}C$	0.96	1.2	1.4	S
	Time	$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$	0.7	1.2	2	s
t _{DL}	Over-Discharge Detection Delay	$T_A = 25^{\circ}C$	120	150	180	ms
	Time	$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$	83	150	255	ms
t _{DIOV}	Discharge Over-Current	$T_A = 25^{\circ}C$	7.2	9	11	ms
	Detection Delay Time	$T_A = -40^{\circ}C$ to $+85^{\circ}C$	5	9	15	ms
t _{CIOV}	Charge Over-Current Detection	$T_A = 25^{\circ}C$	7.2	9	11	ms
	Delay Time	$T_A = -40^{\circ}C$ to $+85^{\circ}C$	5	9	15	ms
t _{SHORT}	Load Short-Circuiting	$T_A = 25^{\circ}C$	240	300	360	us
	Detection Delay Time	$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$	150	300	540	us

Typical Performance Characteristics

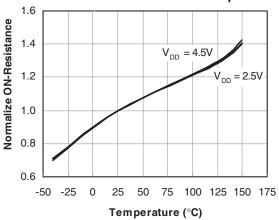


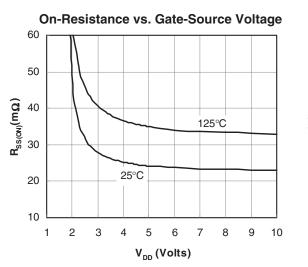


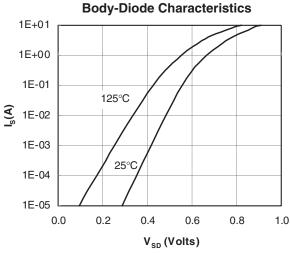
On-Resistance vs. Drain Current and Gate Voltage



On-Resistance vs. Junction Temperature









Theory of Operation

Please refer to the Timing Diagrams for more information.

Normal Status

The AOZ9004D monitors the voltage between the V_{DD} pin and V_{SS} pin and the voltage difference between the V_M pin and V_{SS} pin to control charging and discharging. Since the device only draws a few microamperes of current during operation and the voltage drop across the low-pass filter R1 is negligible, the voltage between V_{DD} and V_{SS} is equal to the battery voltage. When the battery voltage is in the range between over-discharge detection voltage (V_{DL}) and overcharge detection voltage (V_{CU}), and the VM pin voltage is in the range between the charge over-current detection voltage (V_{CIOV}) and discharge over-current detection voltage (V_{DIOV}), the IC turns both the charging and discharging control FETs on. In this normal status, charging and discharging can be carried out freely.

Caution: Products with "Shut-down Function Available" feature may not enable discharging when the battery is connected for the first time. Connect the charger or short V_M pin to V_{SS} can restore the normal status.

Overcharge Status

When the battery voltage rises higher than overcharge detection voltage (V_{CU}) for the overcharge detection delay time (t_{CU}) or longer in the normal status, the AOZ9004D turns off the charging control MOSFET to stop charging. This condition is the overcharge status. The resistance (R_{VMD}) between the V_M pin and V_{DD} pin, and the resistance (R_{VMS}) between the V_M pin and V_{SS} pin are not connected. The overcharge status is released in the following two cases:

- 1. When the battery voltage falls below overcharge release voltage (V_{CL}) and V_M pin voltage is higher than -0.7V (Typ.) (charger is removed), the AOZ9004D turns on the charging control MOSFET and returns to the normal status.
- When a load is connected and battery voltage is below overcharge detection voltage (V_{CU}), the AOZ9004D turns on the charging control MOSFET and returns to the normal status.

Caution: When both charger and load are connected after overcharge detection, charging control FET still remains off and a portion of the load current may flow through body diode of charging control FET if the charger can not supply the full load current. This condition may overheat the charging control FET. Please refer to the Typical Characteristics for more information.

Over-Discharge Status

When the battery voltage falls below over-discharge detection voltage (V_{DL}) for the over-discharge detection delay time (t_{DI}) or longer, the IC turns off the discharging control MOSFET to stop discharging. This condition is the over-discharge status. Under the over-discharge status, the V_M pin voltage is pulled up by the resistor between the V_M pin and V_{DD} pin in the IC (R_{VMD}). The resistance (R_{VMS}) between the V_M pin and V_{SS} pin is not connected in the over-discharge status. When voltage difference between the V_M pin and V_{DD} pin is 1.3V (Typ.) or lower, the productions with "Shut-down Function Available" feature can enter the shut-down status to save power. At this status, the current consumption is reduced to the shut-down current consumption (IPON). The shutdown status is released when a charger is connected and the voltage difference between the V_M pin and V_{DD} pin becomes 1.3V (Typ.) or higher.

When a battery in the over-discharge status is connected to a charger and provides that the VM pin voltage is lower than -0.7V (Typ.), the AOZ9004D releases the over-discharge status and turns on the discharging MOSFET when the battery voltage reaches over-discharge detection voltage (V_{DL}) or higher. If VM pin voltage is not lower than -0.7 V (Typ.), the AOZ9004D releases the over-discharge status and turns on the discharging MOSFET when the battery voltage reaches over-discharge detection voltage (V_{DL}) or higher. If VM pin voltage is not lower than -0.7 V (Typ.), the AOZ9004D releases the over-discharge status and turns on the discharging MOSFET when the battery voltage reaches over-discharge detection voltage (V_{DU}) or higher.

Discharge Over-current Status (Discharge Over-current, Load Short-circuiting)

When a battery is in the normal status, and the discharge current becomes higher than specified value and the status lasts for the discharge over-current detection delay time (t_{DIOV}), the IC turns off the discharge control MOSFET and stops discharging. This status is the discharge over-current status. In the discharge overcurrent status, the V_{M} pin and V_{SS} pin are shorted by the resistor between V_M pin and V_{SS} pin (R_{VMS}) in the IC. When the load is disconnected, the V_M pin returns to the V_{SS} potential. When the impedance between the EB+ pin and EB- pin (Refer to Figure 1) increases and is equal to the impedance that enables automatic restoration and the voltage at the V_M pin returns to discharge overcurrent detection voltage (V_{DIOV}) or lower, the discharge over-current status is restored to the normal status. Even if the connected impedance is smaller than automatic restoration level, the AOZ9004D will be restored to the normal status from discharge over-current detection status when the voltage at the V_M pin becomes the discharge over-current detection voltage (V_{DIOV}) or lower by connecting the charger. The resistance (R_{VMD}) between the V_M pin and V_{DD} pin is not connected in the discharge over-current detection status.

When a battery is in the normal status, and the discharge current becomes abnormally higher (EB+ pin and EB- pin shorted), and thus the V_M pin voltage is equal or higher than load short-circuiting detection voltage (V_{SHORT}) for load short-circuiting detection delay time (t_{SHORT}), the IC turns off the discharge control MOSFET and stops discharging. This status is the load shorting-circuiting status. In the load shorting-circuiting status, the V_M pin and V_{SS} pin are shorted by the resistor between V_M pin and V_{SS} pin (R_{VMS}) in the IC. When the short-circuiting condition is released, the V_M pin returns to the V_{SS} potential. The resistance (R_{VMD}) between the V_M pin and V_{DD} pin is not connected in the load shorting-circuiting status.

Charge Over-Current Status

When a battery in the normal status is in the status, and the charge current is higher than the specified value and the status lasts for the charge over-current detection delay time (t_{CIOV}), the charge control MOSFET is turned off and charging is stopped. This status is the charge over-current status. This IC will be restored to the normal status from the charge over-current status when, the voltage at the V_M pin returns to charge over-current detection voltage (V_{CIOV}) or higher by removing the charger. The charge over-current detection function does not work in the over-discharge status. The resistance (R_{VMD}) between the V_M pin and V_{DD} pin, and the resistance (R_{VMS}) between the V_M pin and V_{SS} pin are not connected in the charge over-current status.

0V Battery Charging Function "Available"

This function is used to recharge a connected battery whose voltage is 0V due to self-discharge. When the 0V battery charge starting charger voltage (V_{0CHA}) or a higher voltage is applied between the EB+ and EB- pins by connecting a charger, the charging control MOSFET gate is fixed to the V_{DD} pin voltage.

When the voltage between the gate and source of the charging control MOSFET becomes equal to or higher than the turn-on voltage due to the charger voltage, the charging control MOSFET is turned on to start charging. At this time, the discharging control MOSFET is off and the charging current flows through the internal parasitic diode in the discharging control MOSFET. When the battery voltage becomes equal to or higher than overdischarge release voltage (V_{DU}), the AOZ9004D enters the normal status.

0V Battery Charging Function "Unavailable"

This function inhibits recharging when a battery that is internally short-circuited (0V battery) is connected. When the battery voltage is the 0V battery charge inhibition battery voltage (V_{0INH}) or lower, the charging control MOSFET gate is fixed to the EB- pin voltage to inhibit charging. When the battery voltage is the 0V battery charge inhibition battery voltage (V_{0INH}) or higher, charging can be performed.



Timing Diagrams

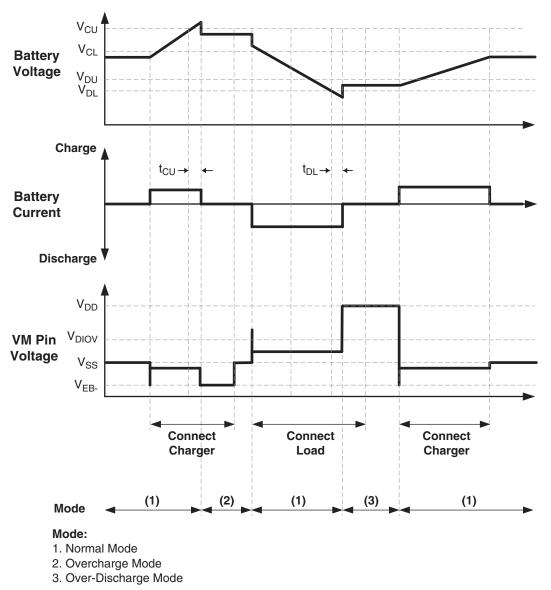


Figure 2. Overcharge and Over-discharge Detection Timing Diagram

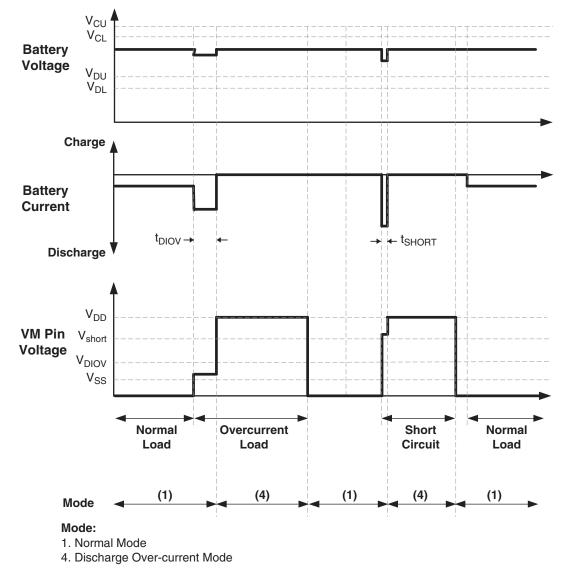


Figure 3. Discharging Over-current Detection Timing Diagram



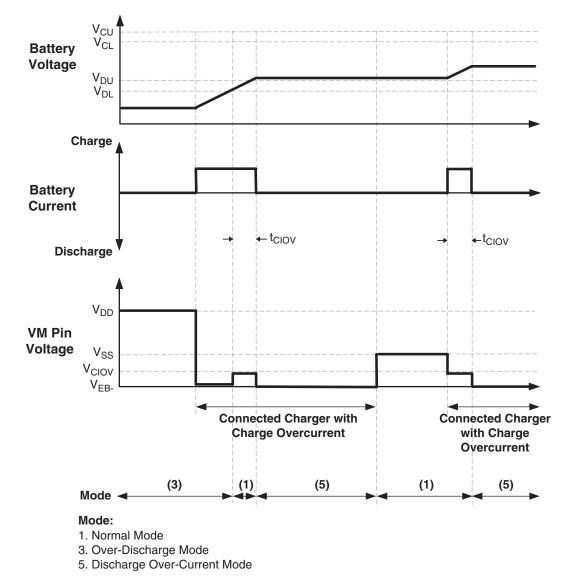


Figure 4. Charging Over-current Detection Timing Diagram



Applications Information

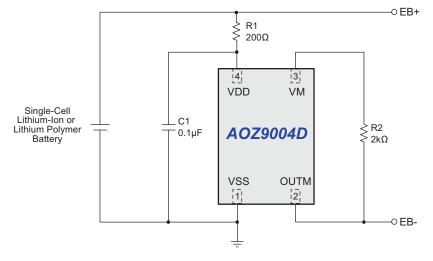


Figure 5. AOZ9004D Applications Circuit

A low-pass filter formed by R1 and C1 reduces supply voltage fluctuation on the VDD pin. R1 also provides ESD protection and serves as an current-limiting resistor in the event of charger reverse connection. The supply current of AOZ9004D has to flow through R1, so a small R1 should be chosen to guarantee detection accuracy of VDD voltage. Choose a resistor value between 100Ω and 330Ω for R1. Choose the value of C1 to be 0.022μ F or higher. Both R1 and C1 should be placed as close as possible to AOZ9004D to minimize parasitic effect.

R2 provides ESD protection and serve as a currentlimiting resistor in the event of charger reverse connection. A large value resistor should be chosen to limit power consumption during this condition. However, an extremely large value of R2, of course, will cause inaccuracy of VM pin voltage detection. Choose a resistor value between 300Ω and $4k\Omega$ for R2.

Designator	Purpose	Min.	Тур.	Max.
C1	Reduce supply voltage fluctuation, provide ESD protection, and limit current when a charger is reversely connected	0.022µF	0.1µF	1.0µF
R1	Reduce supply voltage fluctuation	100Ω	220Ω	330Ω
R2	Provide ESD protection and limit current when a charger is reversely connected	300Ω	2kΩ	4kΩ

Table 3. External Components Selection Range

Dimensions in inches

Nom

0.035

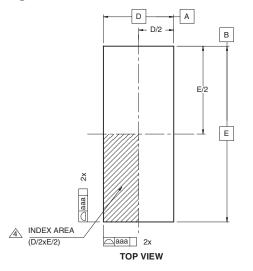
Max.

0.039

Min

0.032

Package Dimensions



A1	0	0.02	0.05	0	0.001	0.002
A3		0.20 REF.			0.008 REF.	
b	0.40	0.45	0.50	0.016	0.018	0.020
D	2.00 BSC				0.079 BSC	
D2	1.30	1.45	1.55	0.051	0.057	0.061
E		5.00 BSC			0.197 BSC	
E2	1.75	1.80	1.85	0.069	0.071	0.073
E3	1.05	1.10	1.15	0.041	0.043	0.045
E4	0.35	0.40	0.45	0.014	0.016	0.018
е		0.95 BSC			0.037 BSC	
L	0.40	0.45	0.50	0.016	0.018	0.020
aaa		0.15			0.006	—
bbb		0.10			0.004	—
CCC		0.10	_		0.004	—

Max.

1.00

Dimensions in millimeters

Nom

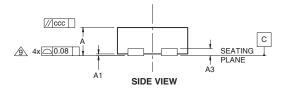
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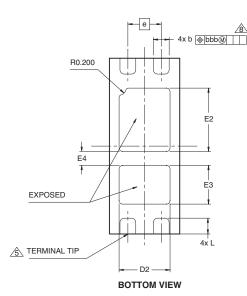
Symbol

А

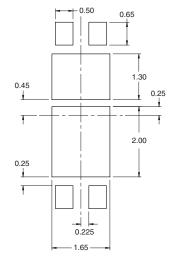
Min.

0.80





RECOMMENDED LAND PATTERN



Notes:

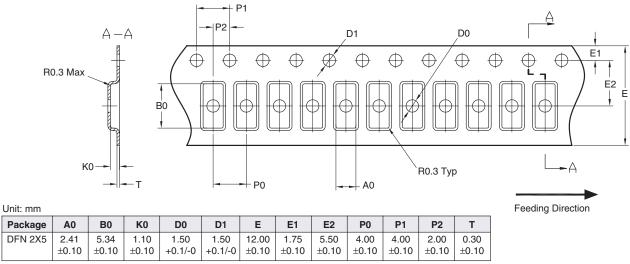
- 1. A, A1, and A3 dimensions and tolerances conform to ASME Y14.5M-1994.
- 2. All dimensions are in millimeters, converted inch dimensions are not necessarily exact.
- 3. N is the total number of terminals.
- \land The terminal #1 identifier and terminal numbering conventions all conform to JEDEC publication 95 SPP-002. Details of terminal #1 identifier are optional, but must be located within the zone indicated. The terminal #1 identifier may be a marked feature.
- 5 ND and NE refer to the number of terminals on each D and E side respectively.
- 6. Depopulation is possible in a symmetrical fashion.
- D, E. b, D2, E2, E3, E4 and L are NON JEDEC REGISTERED. 7.
- 8 Dimension b applied to metallized terminal and is measured between 0.15mm and 0.30mm from the terminal tip. If the terminal has the optional radius on the other end of the terminal, the dimension b should not be measured in that radius area.
- 9. Coplanarity applies to the exposed heat slus as well as the terminals.
- 10. Drawing shown for illustration purposes only.

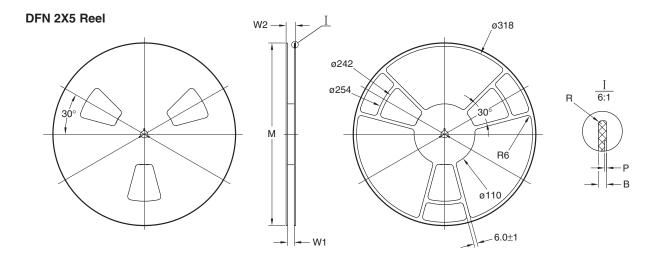
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Tape and Reel Dimensions

DFN2X5 Carrier Tape

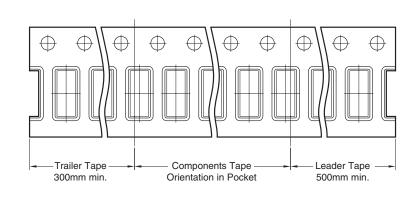




Tape Size	Reel Size	М	W1	W2	в	Ρ	R
12mm	ø330	ø330.00 +0.3/-0.4	12.40 +2.0/-0.0	18.40 Max	2.40 ±0.3	0.5	1

DFN2X5 Tape

Leader/Trailer & Orientation





AOZ9004D Package Marking

